100V 6.2mΩ N-Ch Power MOSFET

Features

- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge, Q_g
- 100% UIS and R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant
- AEC-Q101 Qualified for Automotive Applications

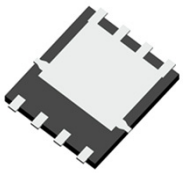
Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th)\_Typ}$	2.7	V
I_D (@ V_{GS} = 10V) (1)	87	A
$R_{DS(ON)\_Typ}$ (@ V_{GS} = 10V)	6.2	mΩ

PDFN5x6-8L

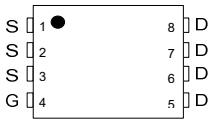
Top View

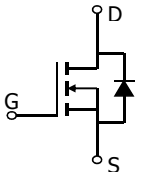
Bottom View



Pin Configuration

Top View





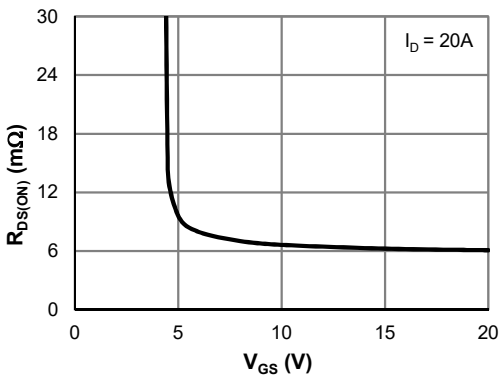
Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH1008AGQ-13	PDFN5x6-8L	8	SH1008AQ	1	-55 to 175	13-inch Reel	3000

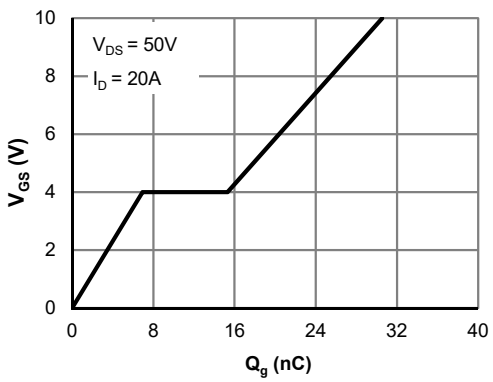
Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	100	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (1)	T_C = 25°C	I_D	87	A
	T_C = 100°C		62	
Pulsed Drain Current (2)		I_{DM}	348	A
Avalanche Current (3)		I_{AS}	31	A
Avalanche Energy (3)		E_{AS}	144	mJ
Power Dissipation (4)	T_C = 25°C	P_D	125	W
	T_C = 100°C		63	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

$R_{DS(ON)}$ vs. V_{GS}



Gate Charge



Electrical Characteristics (@ T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250μA, V_{GS} = 0V	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1.0	μA
		T_J = 55°C			5.0	
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	2.7	4.0	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		6.2	7.8	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 20A		51		S
Diode Forward Voltage	V_{SD}	I_S = 1A, V_{GS} = 0V		0.70	1.0	V
Diode Continuous Current	I_S	T_C = 25°C			125	A
DYNAMIC PARAMETERS [5]						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		1920		pF
Output Capacitance	C_{oss}			445		pF
Reverse Transfer Capacitance	C_{rss}			7.0		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS}= 0V, f = 1MHz		1.5		Ω
SWITCHING PARAMETERS [5]						
Total Gate Charge (@V_{GS} = 10V)	Q_g	V_{GS} = 0 to 10V V_{DS} = 50V, I_D = 20A		30		nC
Total Gate Charge (@V_{GS} = 6.0V)	Q_g			20		nC
Gate Source Charge	Q_{gs}			6.9		nC
Gate Drain Charge	Q_{gd}			8.4		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS} = 10V, V_{DS} = 50V R_L = 2.5Ω, R_{GEN} = 6Ω		9.5		ns
Turn-On Rise Time	t_r			10.2		ns
Turn-Off DelayTime	$t_{D(off)}$			31		ns
Turn-Off Fall Time	t_f			22		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F = 15A, dI_F/dt = 100A/μs		55		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 15A, dI_F/dt = 100A/μs		58		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	48	58	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.2	1.4	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T_{J_Max} = 175°C.
3. This single-pulse measurement was taken under the following condition [L = 300uH, V_{GS} = 10V, V_{DS} = 50V] while its value is limited by T_{J_Max} = 175°C.
4. The power dissipation P_D is based on T_{J_Max} = 175°C.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

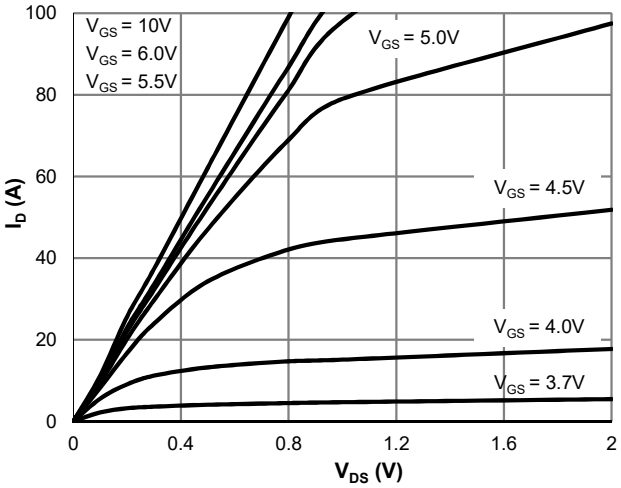


Figure 1: Saturation Characteristics

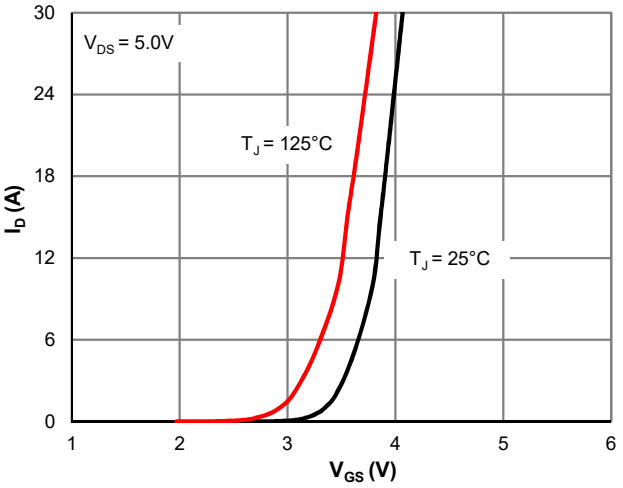


Figure 2: Transfer Characteristics

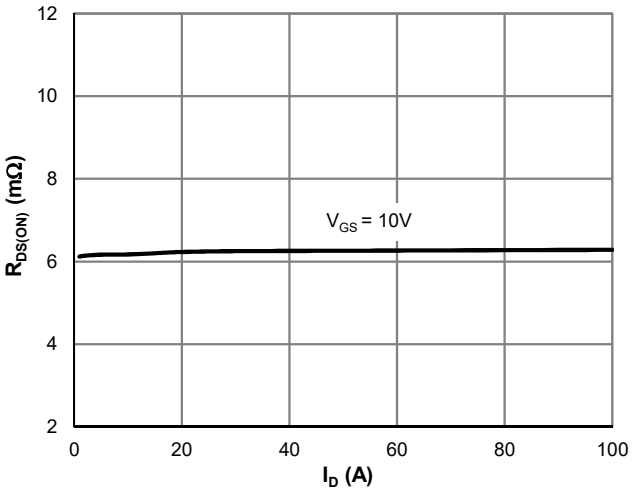


Figure 3: $R_{DS(ON)}$ vs. Drain Current

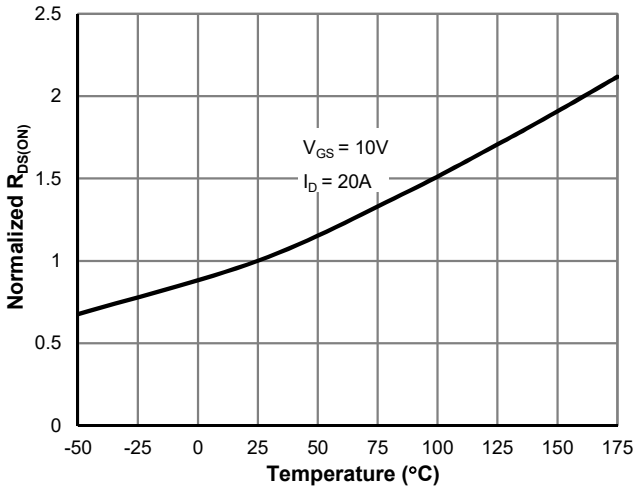


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

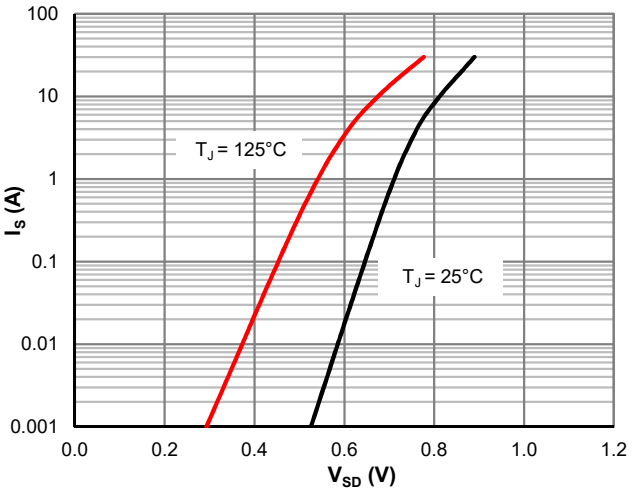


Figure 5: Body-Diode Characteristics

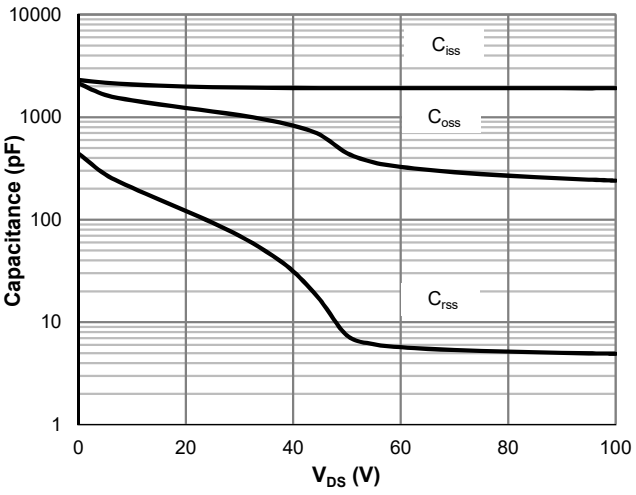


Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

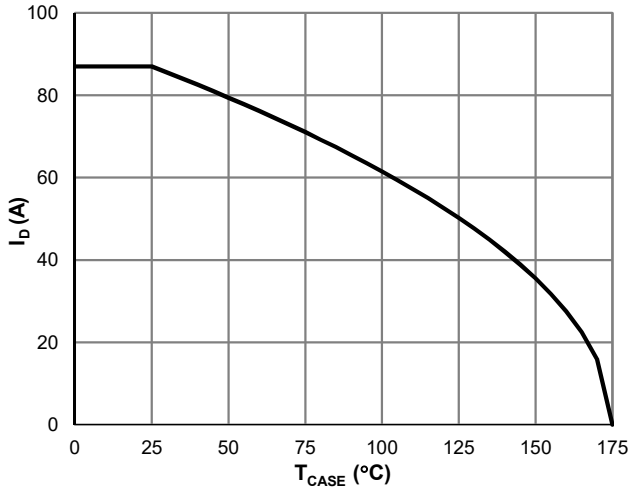


Figure 7: Current De-rating

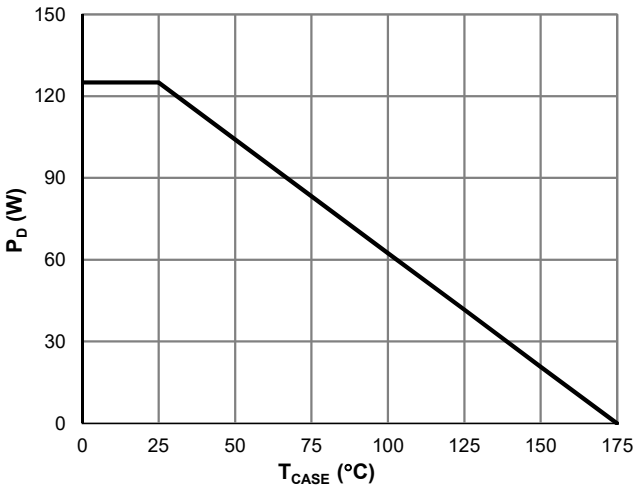


Figure 8: Power De-rating

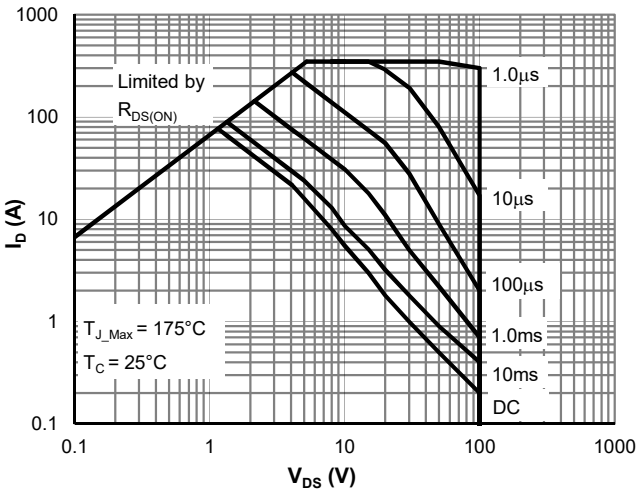


Figure 9: Maximum Safe Operating

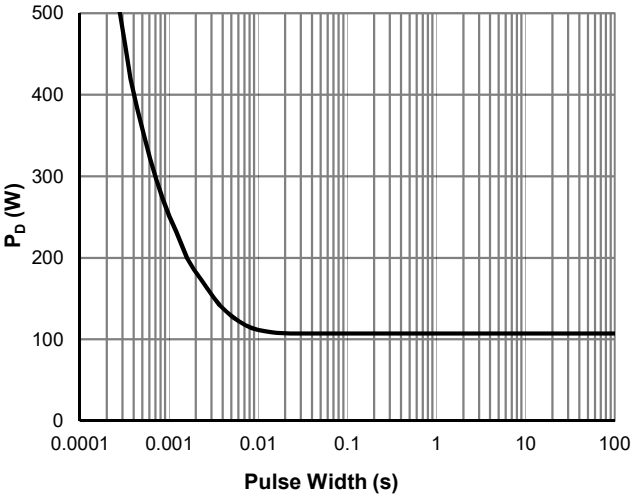


Figure 10: Single Pulse Power Rating, Junction-to-Case

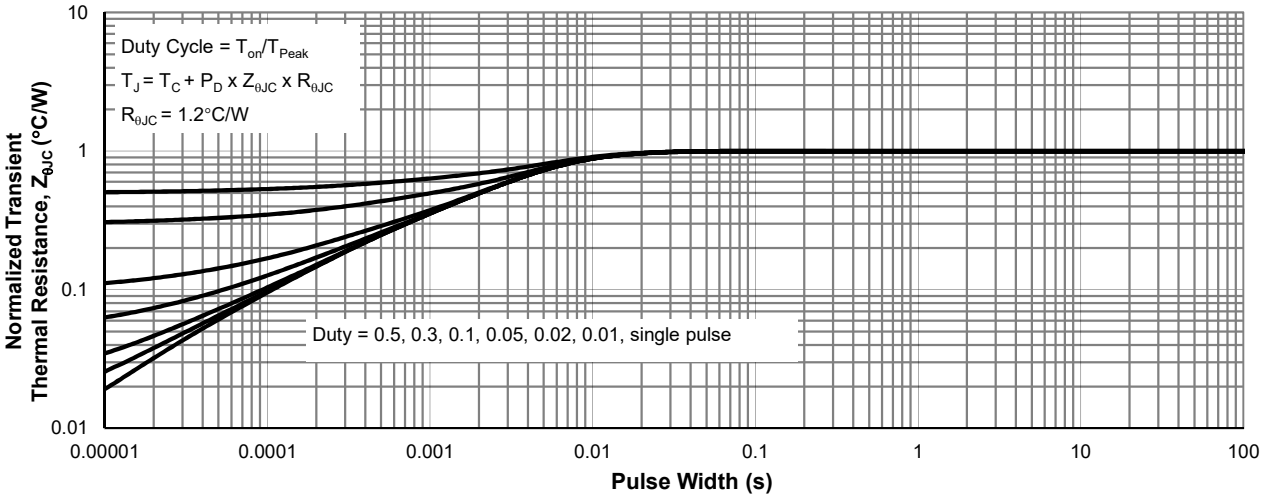
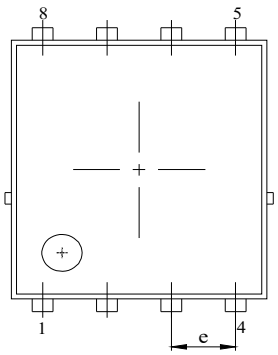


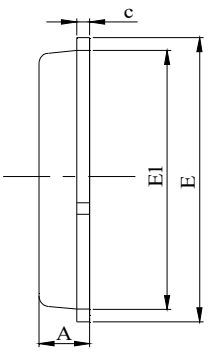
Figure 11: Normalized Maximum Transient Thermal Impedance

PDFN5x6-8L Package Information

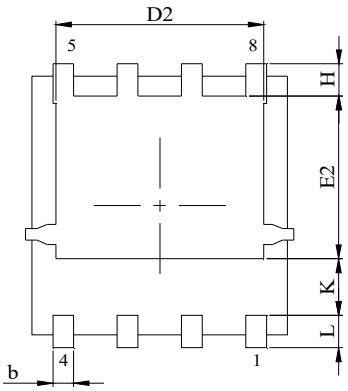
Package Outline



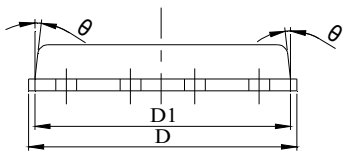
Top View



Side View



Bottom View

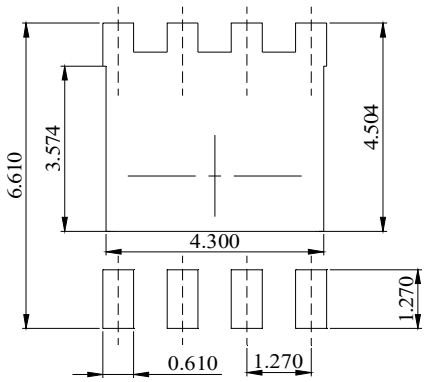


Front View

NOTES:
1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions D1 and E1 do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.31	0.41	0.51
c	0.20	0.25	0.30
D	5.00	5.20	5.40
D1	4.95	5.05	5.15
D2	4.00	4.10	4.20
E	6.05	6.15	6.25
E1	5.50	5.60	5.70
E2	3.42	3.53	3.63
e		1.27BSC	
H	0.60	0.70	0.80
L	0.50	0.70	0.80
θ	-	-	10°

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS